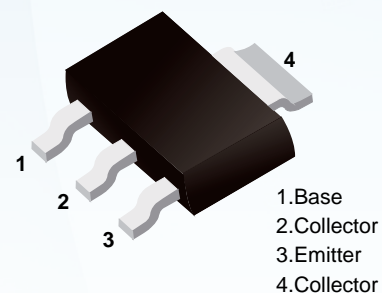


## ■ PNP Transistors

### ■ Features

- For AF driver and output stages
- High collector current
- Low collector-emitter saturation voltage
- Complementary to BCP54,BCP55,BCP56



■ Simplified outline(SOT-223)

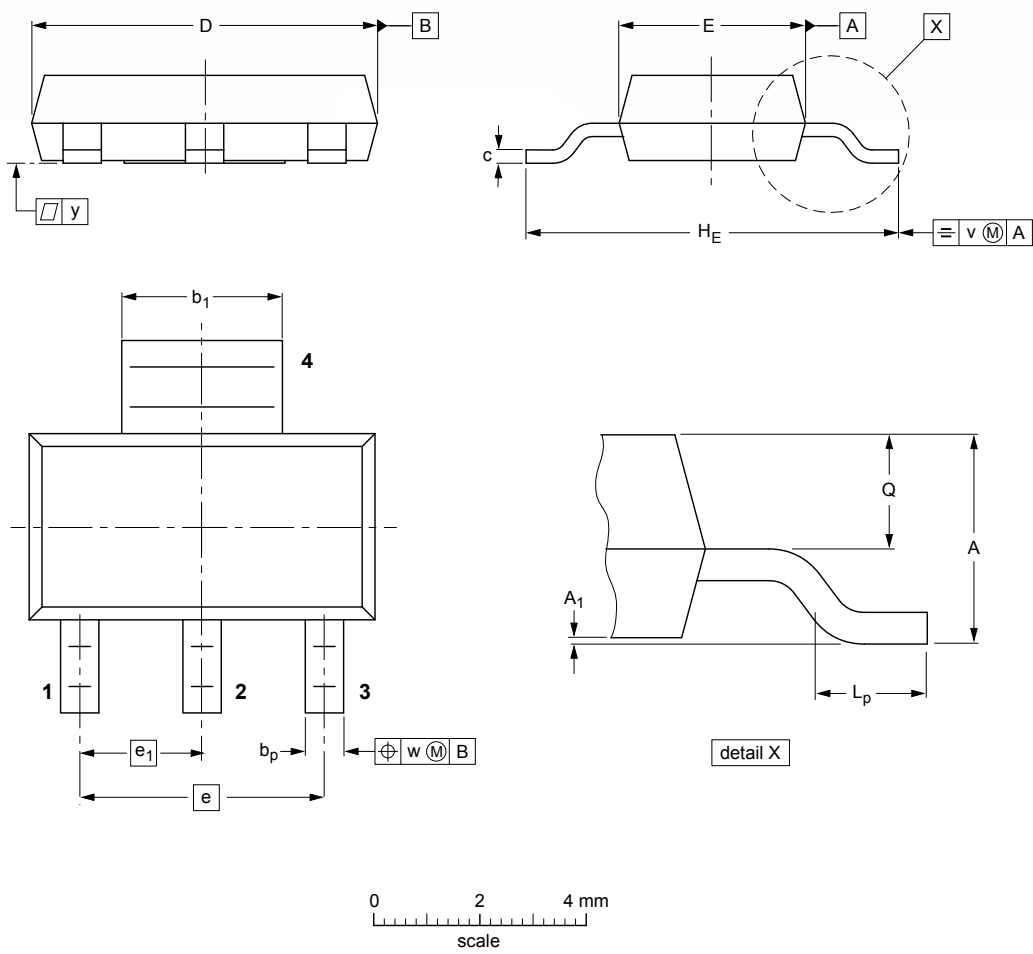
### ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	BCP51	BCP52	BCP53	Unit
Collector - Base Voltage	V <sub>CBO</sub>	-45	-60	-100	V
Collector - Emitter Voltage	V <sub>CEO</sub>	-45	-60	-80	
Emitter - Base Voltage	V <sub>EBO</sub>	-5			
Collector Current - Continuous	I <sub>C</sub>	-1			A
Collector Power Dissipation	P <sub>C</sub>	1.5			W
Thermal Resistance Junction to Ambient	R <sub>θJA</sub>	94			°C/W
Junction Temperature	T <sub>J</sub>	150			°C
Storage Temperature Range	T <sub>stg</sub>	-65 to 150			

**■ Electrical Characteristics Ta = 25°C**

Parameter		Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	BCP51	V <sub>CBO</sub>	I <sub>C</sub> = -100 μA, I <sub>E</sub> = 0	-45			V
	BCP52			-60			
	BCP53			-100			
Collector- emitter breakdown voltage	BCP51	V <sub>CEO</sub>	I <sub>C</sub> = -10 mA, I <sub>B</sub> = 0	-45			V
	BCP52			-60			
	BCP53			-80			
Emitter - base breakdown voltage		V <sub>EBO</sub>	I <sub>E</sub> = -100 μA, I <sub>C</sub> = 0	-5			
Collector-base cut-off current	BCP51	I <sub>CBO</sub>	V <sub>CB</sub> = -45 V, I <sub>E</sub> = 0			-0.1	uA
	BCP52		V <sub>CB</sub> = -60 V, I <sub>E</sub> = 0				
	BCP53		V <sub>CB</sub> = -100 V, I <sub>E</sub> = 0				
Emitter cut-off current		I <sub>EBO</sub>	V <sub>EB</sub> = -5V, I <sub>C</sub> =0			-0.1	
Collector-emitter saturation voltage		V <sub>CE(sat)</sub>	I <sub>C</sub> =-500 mA, I <sub>B</sub> =-50mA			-0.5	V
Base - emitter saturation voltage		V <sub>BE(sat)</sub>	I <sub>C</sub> =-500 mA, I <sub>B</sub> =-50mA			-1.2	
Base-emitter voltage		V <sub>BE</sub>	V <sub>CE</sub> = -2V, I <sub>C</sub> = -500mA			-1	
DC current gain	h <sub>FE(1)</sub>		V <sub>CE</sub> = -2V, I <sub>C</sub> = -5mA	25			
	h <sub>FE(2)</sub>		V <sub>CE</sub> = -2V, I <sub>C</sub> = -150mA	63		250	
	h <sub>FE(3)</sub>		V <sub>CE</sub> = -2V, I <sub>C</sub> = -500mA	25			
Transition frequency		f <sub>T</sub>	V <sub>CE</sub> = -10V, I <sub>C</sub> = -50mA, f=100MHz	100			MHz

■ SOT-223



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub>	b <sub>p</sub>	b <sub>1</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w	y
mm	1.8 1.5	0.10 0.01	0.80 0.60	3.1 2.9	0.32 0.22	6.7 6.3	3.7 3.3	4.6	2.3	7.3 6.7	1.1 0.7	0.95 0.85	0.2	0.1	0.1

## Disclaimer

EVVOSEMI ("EVVO") reserves the right to make corrections, enhancements, improvements, and other changes to its products and services at any time, and to discontinue any product or service without notice.

EVVO warrants the performance of its hardware products to the specifications applicable at the time of sale in accordance with its standard warranty. Testing and other quality control techniques are used as deemed necessary by EVVO to support this warranty. Except where mandated by government requirements, testing of all parameters of each product is not necessarily performed.

Customers should obtain and confirm the latest product information and specifications before final design, purchase, or use. EVVO makes no warranty, representation, or guarantee regarding the suitability of its products for any particular purpose, nor does EVVO assume any liability for application assistance or customer product design. EVVO does not warrant or accept any liability for products that are purchased or used for any unintended or unauthorized application.

EVVO products are not authorized for use as critical components in life support devices or systems without the express written approval of EVVOSEMI.

The EVVO logo and EVVOSEMI are trademarks of EVVOSEMI or its subsidiaries in relevant jurisdictions. EVVO reserves the right to make changes without further notice to any products herein.